THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Thermal Resistance,	Junction−to−Case Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds		T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

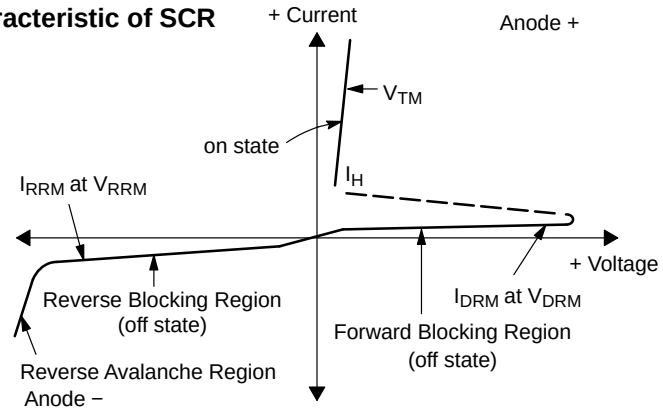
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current (V_D = Rated V_{DRM} and V_{RRM}; Gate Open)	T_J = 25°C T_J = 125°C	I_{DRM}, I_{RRM}	− −	− −	0.01 2.0	mA
ON CHARACTERISTICS						
Peak Forward On−State Voltage (Note 2) (I_{TM} = 24 A)		V_{TM}	−	−	2.2	V
Gate Trigger Current (Continuous dc) (V_D = 12 V; R_L = 100 Ω)		I_{GT}	2.0	8.0	20	mA
Holding Current (V_D = 12 V, Gate Open, Initiating Current = 200 mA)		I_H	4.0	20	40	mA
Latch Current (V_D = 12 V, I_G = 20 mA)		I_L	6.0	25	60	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V; R_L =100 Ω)		V_{GT}	0.5	0.65	1.0	V
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off−State Voltage (V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)		dv/dt	100	250	−	V/μs
Repetitive Critical Rate of Rise of On−State Current IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, Igt = 50 mA		di/dt	−	−	50	A/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

Voltage Current Characteristic of SCR



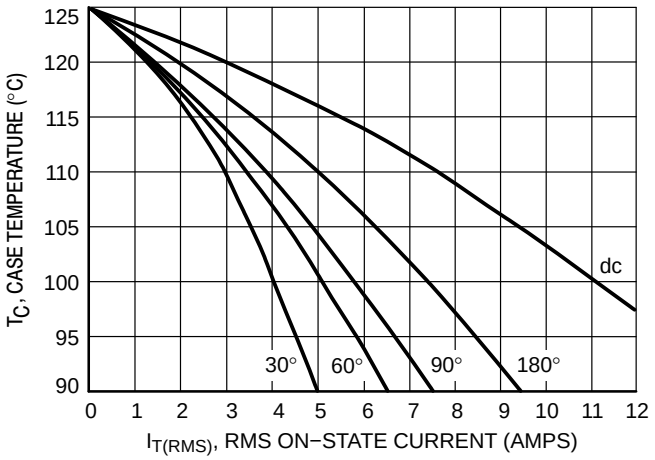


Figure 1. Typical RMS Current Derating

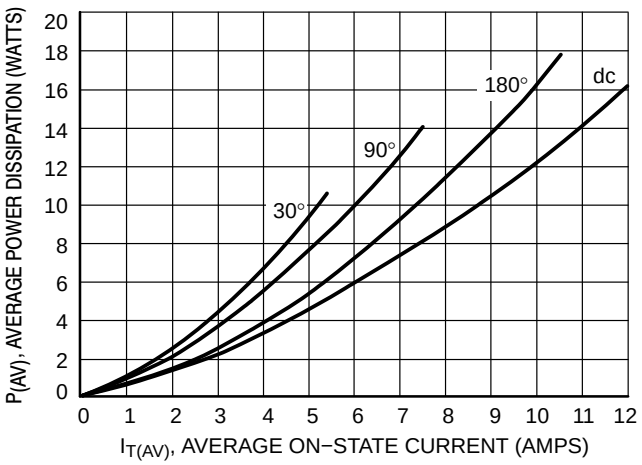


Figure 2. On−State Power Dissipation

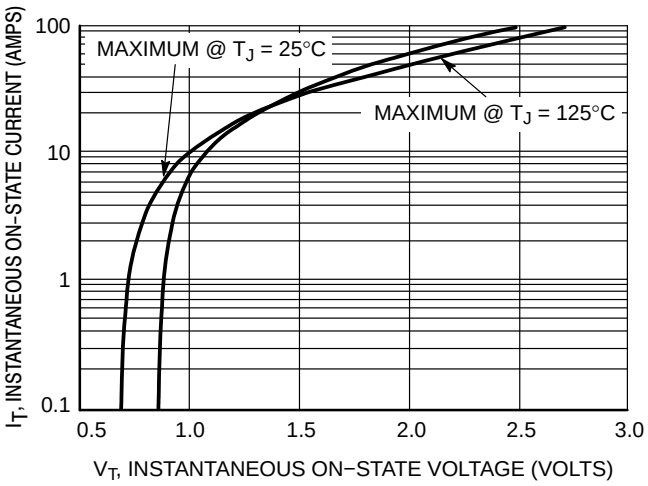


Figure 3. Typical On−State Characteristics

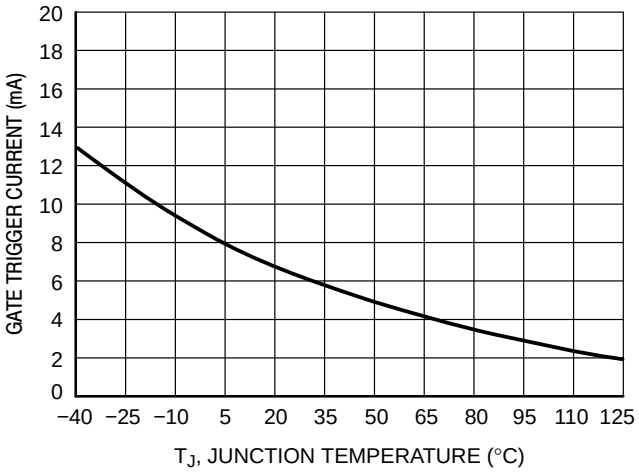


Figure 4. Typical Gate Trigger Current versus Junction Temperature

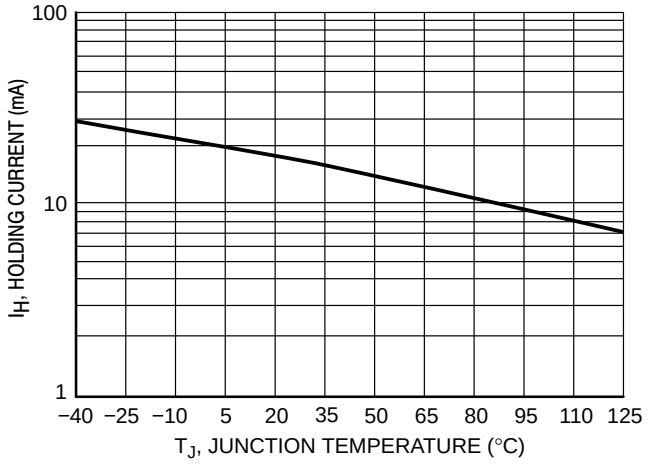


Figure 5. Typical Holding Current versus Junction Temperature

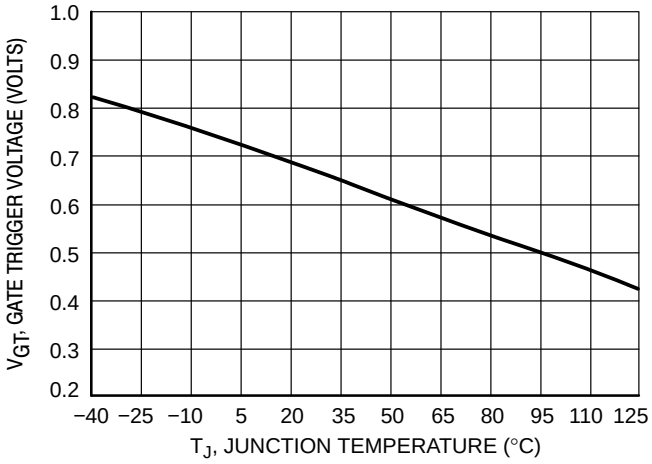


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

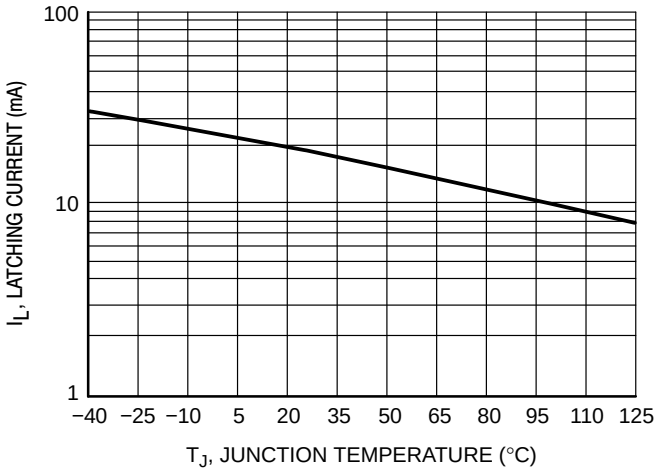
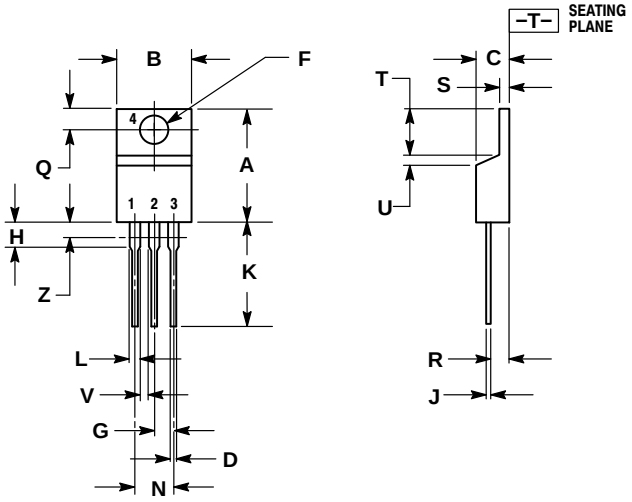


Figure 7. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

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